

Simoen Eddy

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/4893958/simoen-eddy-publications-by-year.pdf>

Version: 2024-04-25

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

140
papers

1,530
citations

19
h-index

32
g-index

152
ext. papers

1,860
ext. citations

2.3
avg, IF

4.53
L-index

#	Paper	IF	Citations
140	Design of operational transconductance amplifier with Gate-All-Around Nanosheet MOSFET using experimental data from room temperature to 200°C. <i>Solid-State Electronics</i> , 2022 , 189, 108238	1.7	0
139	On the asymmetry of the DC and low-frequency noise characteristics of vertical nanowire MOSFETs with bulk source contact. <i>Solid-State Electronics</i> , 2022 , 191, 108268	1.7	0
138	Trade-off analysis between gm/ID and FT of nanosheet NMOS transistors with different metal gate stack at high temperature. <i>Solid-State Electronics</i> , 2022 , 191, 108267	1.7	0
137	Impact of the Channel Doping on the Low-Frequency Noise of Silicon Vertical Nanowire pFETs. <i>Solid-State Electronics</i> , 2022 , 108318	1.7	0
136	DC and low a frequency noise analysis of p channel gate all around vertically stacked silicon nanosheets. <i>Solid-State Electronics</i> , 2022 , 108360	1.7	0
135	Linking Room- and Low-Temperature Electrical Performance of MOS Gate Stacks for Cryogenic Applications. <i>IEEE Electron Device Letters</i> , 2022 , 43, 674-677	4.4	0
134	Analysis of semi-insulating carbon-doped GaN layers using deep-level transient spectroscopy. <i>Journal of Applied Physics</i> , 2021 , 130, 205701	2.5	0
133	Low temperature investigation of n-channel GAA vertically stacked silicon nanosheets 2021 ,		2
132	Interfacial Properties of nMOSFETs With Different Al ₂ O ₃ Capping Layer Thickness and TiN Gate Stacks. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 948-953	2.9	1
131	Alleviation of Negative-Bias Temperature Instability in Si p-FinFETs With ALD W Gate-Filling Metal by Annealing Process Optimization. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 1-1	2.3	1
130	Analog Figures of Merit of Vertically Stacked Silicon Nanosheets nMOSFETs With Two Different Metal Gates for the Sub-7 nm Technology Node Operating at High Temperatures. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 3630-3635	2.9	10
129	Current mirror designed with GAA nanosheet MOSFETs from room temperature to 200 °C. <i>Semiconductor Science and Technology</i> , 2021 , 36, 095019	1.8	1
128	Recovery Behavior of Interface Traps After Negative Bias Temperature Instability Stress in p-FinFETs Featuring Fast Trap Characterization Technique. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 4251-4258	2.9	1
127	Low-Frequency noise investigation of AlGaIn/GaN high-electron-mobility transistors. <i>Solid-State Electronics</i> , 2021 , 183, 108050	1.7	0
126	Low frequency noise performance of horizontal, stacked and vertical silicon nanowire MOSFETs. <i>Solid-State Electronics</i> , 2021 , 184, 108087	1.7	3
125	Low-frequency noise assessment of ferro-electric field-effect transistors with Si-doped HfO ₂ gate dielectric. <i>AIP Advances</i> , 2021 , 11, 015219	1.5	1
124	Temperature-Dependent Electrical Properties of nMOSFETs With Different Thickness Al ₂ O ₃ Capping Layer and TiN Gate. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 6020-6025	2.9	0

123	Understanding Frequency Dependence of Trap Generation Under AC Negative Bias Temperature Instability Stress in Si p-FinFETs. <i>IEEE Electron Device Letters</i> , 2020 , 41, 965-968	4.4	7
122	Low-Frequency Noise Characterization of Germanium n-Channel FinFETs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 2872-2877	2.9	5
121	A Deep Level Transient Spectroscopy Study of Hole Traps in GeSe _{1-x} -based Layers for Ovonic Threshold Switching Selectors. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 044006	2	
120	Intrinsic Voltage Gain of Stacked GAA Nanosheet MOSFETs Operating at High Temperatures. <i>ECS Transactions</i> , 2020 , 97, 65-69	1	2
119	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2020 , 20, 498-505	1.6	1
118	Low-Frequency Noise Investigation of GaN/AlGa _N MetalOxideSemiconductor High-Electron-Mobility Field-Effect Transistor With Different Gate Length and Orientation. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3062-3068	2.9	8
117	Analog design with Line-TFET device experimental data: from device to circuit level. <i>Semiconductor Science and Technology</i> , 2020 , 35, 055025	1.8	7
116	Improved physics-based analysis to discriminate the flicker noise origin at very low temperature and drain voltage polarization. <i>Solid-State Electronics</i> , 2020 , 171, 107771	1.7	2
115	Electrical Activity of Extended Defects in Relaxed In _x Ga _{1-x} As Hetero-Epitaxial Layers. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 033001	2	0
114	An Investigation of Field Reduction Effect on NBTI Parameter Characterization and Lifetime Prediction Using a Constant Field Stress Method. <i>IEEE Transactions on Device and Materials Reliability</i> , 2020 , 20, 92-96	1.6	3
113	LowFrequency Noise in Vertically Stacked Si nChannel Nanosheet FETs. <i>IEEE Electron Device Letters</i> , 2020 , 41, 317-320	4.4	10
112	Comparative study on NBTI kinetics in Si p-FinFETs with B ₂ H ₆ -based and SiH ₄ -based atomic layer deposition tungsten (ALD W) filling metal. <i>Microelectronics Reliability</i> , 2020 , 107, 113627	1.2	3
111	Overview of Bias Temperature Instability in Scaled DRAM Logic for Memory Transistors. <i>IEEE Transactions on Device and Materials Reliability</i> , 2020 , 20, 258-268	1.6	5
110	Characterization of defect states in Mg-doped GaN-on-Si p+n diodes using deep-level transient Fourier spectroscopy. <i>Semiconductor Science and Technology</i> , 2020 , 36, 024002	1.8	0
109	Parasitic subthreshold drain current and low frequency noise in GaN/AlGa _N metal-oxide-semiconductor high-electron-mobility field-effect-transistors. <i>Semiconductor Science and Technology</i> , 2020 , 36, 024003	1.8	0
108	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4827-4833	2.9	4
107	Defect profiling in FEFET Si:HfO ₂ layers. <i>Applied Physics Letters</i> , 2020 , 117, 203504	3.4	8
106	Deep-Level Transient Spectroscopy of GaAs Nanoridge Diodes Grown on Si Substrates. <i>Physical Review Applied</i> , 2020 , 14,	4.3	2

105	Impact of Dummy Gate Removal and a Silicon Cap on the Low-Frequency Noise Performance of Germanium nFinFETs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4713-4719	2.9	6
104	Low-Frequency Noise Assessment of Vertically Stacked Si n-Channel Nanosheet FETs With Different Metal Gates. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4802-4807	2.9	8
103	Using the Octagonal Layout Style for MOSFETs to Boost the Device Matching in Ionizing Radiation Environments. <i>IEEE Transactions on Device and Materials Reliability</i> , 2020 , 20, 754-759	1.6	1
102	Impact of In Situ Annealing on the Deep Levels in Ni-Au/AlN/Si Metal/Insulator/Semiconductor Capacitors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1900248	1.6	3
101	Deep levels in metal/oxide/semiconductor capacitors fabricated on n-type In _{0.53} Ga _{0.47} As lattice matched to InP substrates. <i>Semiconductor Science and Technology</i> , 2019 , 34, 075024	1.8	1
100	Comparison between proton irradiated triple gate SOI TFETs and finfets from a TID point of view. <i>Semiconductor Science and Technology</i> , 2019 , 34, 065003	1.8	2
99	Analysis of Leakage Mechanisms in AlN Nucleation Layers on p-Si and p-SOI Substrates. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1849-1855	2.9	8
98	Low-Frequency Noise Assessment of Work Function Engineering Cap Layers in High-k Gate Stacks. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, N25-N31	2	9
97	Impact of Device Architecture and Gate Stack Processing on the Low-Frequency Noise of Silicon Nanowire Transistors 2019 ,		1
96	Reliability Engineering Enabling Continued Logic for Memory Device Scaling 2019 ,		4
95	A DLTS Perspective on Electrically Active Defects in Plated Crystalline Silicon n+p Solar Cells. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P693-P698	2	1
94	Can we optimize the gate oxide quality of DRAM input/output pMOSFETs by a post-deposition treatment?. <i>Semiconductor Science and Technology</i> , 2019 , 34, 015017	1.8	
93	Gate Metal and Cap Layer Effects on Ge nMOSFETs Low-Frequency Noise Behavior. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1050-1056	2.9	4
92	Detailed characterisation of Si Gate-All-Around Nanowire MOSFETs at cryogenic temperatures. <i>Solid-State Electronics</i> , 2018 , 143, 27-32	1.7	11
91	. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1487-1492	2.9	11
90	Deep Level Assessment of n-Type Si/SiO ₂ Metal-Oxide-Semiconductor Capacitors with Embedded Ge Quantum Dots. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P24-P28	2	1
89	Detailed structural and electrical characterization of plated crystalline silicon solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2018 , 184, 57-66	6.4	12
88	Low Frequency Noise Analysis of Impact of Metal Gate Processing on the Gate Oxide Stack Quality. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q26-Q32	2	7

87	Investigation of Preexisting and Generated Defects in Nonfilamentary a-Si/TiO ₂ RRAM and Their Impacts on RTN Amplitude Distribution. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 970-977	2.9	11
86	Do we have to worry about extended defects in high-mobility materials? 2018 ,		1
85	Impact of ALD TiN Capping Layer on Interface Trap and Channel Hot Carrier Reliability of HKMG nMOSFETs. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1129-1132	4.4	6
84	TaN Versus TiN Metal Gate Input/Output pMOSFETs: A Low-Frequency Noise Perspective. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3676-3681	2.9	6
83	Dry etch damage in n-type crystalline silicon wafers assessed by deep-level transient spectroscopy and minority carrier lifetime. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 041201	1.3	4
82	Impact of band to band tunneling in In _{0.53} Ga _{0.47} As tunnel diodes on the deep level transient spectra. <i>Applied Physics Letters</i> , 2018 , 113, 232101	3.4	1
81	Dry Passivation Process for Silicon Heterojunction Solar Cells Using Hydrogen Plasma Treatment Followed by In Situ a-Si:H Deposition. <i>IEEE Journal of Photovoltaics</i> , 2018 , 8, 1539-1545	3.7	9
80	Physical Mechanism Underlying the Time Exponent Shift in the Ultra-fast NBTI of High-k/Metal gated p-CMOSFETs 2018 ,		4
79	Low-frequency noise measurements at liquid helium temperature operation in ultra-thin buried oxide transistors [Physical interpretation of transport phenomena. <i>Solid-State Electronics</i> , 2018 , 150, 1-7	1.7	5
78	Low frequency noise assessment in n- and p-channel sub-10nm triple-gate FinFETs: Part I: Theory and methodology. <i>Solid-State Electronics</i> , 2017 , 128, 102-108	1.7	14
77	Deep level investigation of INGAAS on INP layer 2017 ,		2
76	On trap identification in triple-gate FinFETs and Gate-All-Around nanowire MOSFETs using low frequency noise spectroscopy 2017 ,		4
75	Insights into the reliability of Ni/Cu plated p-PERC silicon solar cells. <i>Energy Procedia</i> , 2017 , 124, 862-868	2.3	3
74	Calibration of Bulk Trap-Assisted Tunneling and Shockley-Read-Hall Currents and Impact on InGaAs Tunnel-FETs. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3622-3626	2.9	23
73	The Influence of Oxide Thickness and Indium Amount on the Analog Parameters of InxGa1-xAs nTFETs. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3595-3600	2.9	3
72	Low frequency noise assessment in n- and p-channel sub-10nm triple-gate FinFETs: Part II: Measurements and results. <i>Solid-State Electronics</i> , 2017 , 128, 109-114	1.7	10
71	Study of line-TFET analog performance comparing with other TFET and MOSFET architectures. <i>Solid-State Electronics</i> , 2017 , 128, 43-47	1.7	19
70	Impact of the silicon substrate resistivity and growth condition on the deep levels in Ni-Au/AlN/Si MIS Capacitors. <i>Semiconductor Science and Technology</i> , 2017 , 32, 105002	1.8	2

69	Treatments for reliability improvement in thick oxides diffusion and gate replacement I/O transistors. <i>International Journal of Materials Engineering Innovation</i> , 2017 , 8, 53	0.9	7
68	Study of Electron Traps Associated With Oxygen Superlattices in n-Type Silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017 , 14, 1700136		
67	Low-Frequency Noise Assessment of Different Ge pFinFET STI Processes. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4031-4037	2.9	6
66	. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1092-1095	4.4	6
65	Electrical Effects of a Single Extended Defect in MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 3069-3075	2.9	7
64	Defect engineering for shallow n-type junctions in germanium: Facts and fiction. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 2799-2808	1.6	13
63	Comparative analysis of the intrinsic voltage gain and unit gain frequency between SOI and bulk FinFETs up to high temperatures. <i>Solid-State Electronics</i> , 2016 , 123, 124-129	1.7	5
62	Low-Frequency Noise Assessment of the Oxide Trap Density in Thick-Oxide Input-Output Transistors for DRAM Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, N27-N31	2	10
61	Impact of the Effective Work Function Gate Metal on the Low-Frequency Noise of Gate-All-Around Silicon-on-Insulator NWFETs. <i>IEEE Electron Device Letters</i> , 2016 , 37, 363-365	4.4	14
60	Review Device Assessment of Electrically Active Defects in High-Mobility Materials. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P3149-P3165	2	10
59	. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 265-271	2.9	12
58	Comparison between Si/SiO ₂ mid-gap interface states and deep levels associated with silicon-oxygen superlattices in p-type silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 718-723		1
57	(Invited) Gate-All-Around Nanowire FETs vs. Triple-Gate FinFETs: On Gate Integrity and Device Characteristics. <i>ECS Transactions</i> , 2016 , 72, 85-95	1	19
56	Probing the effect of point defects on the leakage blocking capability of Al _{0.1} Ga _{0.9} N/Si structures using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2016 , 120, 215702	2.5	14
55	Comparative Study of Current Transients in HPHT and CVD Diamond Capacitor-Sensors. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P3101-P3107	2	0
54	Low frequency noise and fin width study of silicon passivated germanium pFinFETs 2016 ,		1
53	Effective hole mobility and low-frequency noise characterization of Ge pFinFETs 2016 ,		3
52	Towards single-trap spectroscopy: Generation-recombination noise in UTBOX SOI nMOSFETs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 292-298		10

51	Analytical Techniques for Electrically Active Defect Detection. <i>Semiconductors and Semimetals</i> , 2015 , 91, 205-250	0.6	18
50	Low-Frequency Noise Characterization of GeOx Passivated Germanium MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2078-2083	2.9	13
49	Gate-all-around NWFETs vs. triple-gate FinFETs: Junctionless vs. extensionless and conventional junction devices with controlled EWF modulation for multi-VT CMOS 2015 ,		29
48	Influence of the Source Composition on the Analog Performance Parameters of Vertical Nanowire-TFETs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 16-22	2.9	22
47	Different stress techniques and their efficiency on triple-gate SOI n-MOSFETs. <i>Solid-State Electronics</i> , 2015 , 103, 209-215	1.7	2
46	Impact of thermal budget on the low-frequency noise of DRAM peripheral nMOSFETs 2015 ,		2
45	Border Traps in InGaAs nMOSFETs Assessed by Low-Frequency Noise. <i>IEEE Electron Device Letters</i> , 2014 , 35, 720-722	4.4	9
44	Assessment of the Impact of Inelastic Tunneling on the Frequency-Depth Conversion from Low-Frequency Noise Spectra. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 634-637	2.9	15
43	(Invited) Replacement Metal Gate/High-k Last Technology for Aggressively Scaled Planar and FinFET-Based Devices. <i>ECS Transactions</i> , 2014 , 61, 225-235	1	6
42	Low-frequency noise assessment in advanced UTBOX SOI nMOSFETs with different gate dielectrics. <i>Solid-State Electronics</i> , 2014 , 97, 14-22	1.7	20
41	Deep-level transient spectroscopy of Al/a-Si:H/c-Si structures for heterojunction solar cell applications. <i>Journal of Applied Physics</i> , 2014 , 116, 234501	2.5	9
40	Direct estimation of capture cross sections in the presence of slow capture: application to the identification of quenched-in deep-level defects in Ge. <i>Semiconductor Science and Technology</i> , 2014 , 29, 125007	1.8	7
39	Low-frequency noise analysis of DRAM peripheral transistors with La cap 2014 ,		3
38	Low-frequency noise assessment of border traps in Al ₂ O ₃ capped DRAM peripheral MOSFETs. <i>Semiconductor Science and Technology</i> , 2014 , 29, 115015	1.8	13
37	A new high-k/metal gate CMOS integration scheme (Diffusion and Gate Replacement) suppressing gate height asymmetry and compatible with high-thermal budget memory technologies 2014 ,		7
36	Low-Frequency-Noise-Based Oxide Trap Profiling in Replacement High- κ Metal-Gate pMOSFETs. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q127-Q131	2	9
35	Experimental Comparison Between Trigate p-TFET and p-FinFET Analog Performance as a Function of Temperature. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2493-2497	2.9	46
34	DC and low frequency noise performances of SOI p-FinFETs at very low temperature. <i>Solid-State Electronics</i> , 2013 , 90, 160-165	1.7	15

33	Sidewall crystalline orientation effect of post-treatments for a replacement metal gate bulk fin field effect transistor. <i>ACS Applied Materials & Interfaces</i> , 2013 , 5, 8865-8	9.5	14
32	. <i>IEEE Transactions on Device and Materials Reliability</i> , 2013 , 13, 444-455	1.6	54
31	Low Frequency Noise Analysis for Post-Treatment of Replacement Metal Gate. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 2960-2962	2.9	12
30	Low-frequency noise of n-type triple gate FinFETs fabricated on standard and 45°rotated substrates. <i>Solid-State Electronics</i> , 2013 , 90, 121-126	1.7	3
29	Impact of Al ₂ O ₃ position on performances and reliability in high-k metal gated DRAM periphery transistors 2013 ,		3
28	. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1272-1278	2.9	12
27	Influence of 60-MeV Proton-Irradiation on Standard and Strained n- and p-Channel MuGFETs. <i>IEEE Transactions on Nuclear Science</i> , 2012 , 59, 707-713	1.7	7
26	Challenges and opportunities in advanced Ge pMOSFETs. <i>Materials Science in Semiconductor Processing</i> , 2012 , 15, 588-600	4.3	61
25	Electrically active defects at AlN/Si interface studied by DLTS and ESR. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 1851-1856	1.6	13
24	A DLTS Study of SiO ₂ and SiO ₂ /SiN _x Surface Passivation of Silicon. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H612	3.9	18
23	A deep-level analysis of Ni ²⁺ /AlN/(1 1 1) p+-Si metal-insulator-semiconductor capacitors. <i>Journal Physics D: Applied Physics</i> , 2011 , 44, 475104	3	12
22	Investigation of Light-Induced Deep-Level Defect Activation at the AlN/Si Interface. <i>Applied Physics Express</i> , 2011 , 4, 094101	2.4	11
21	Impact of Forming Gas Annealing and Firing on the Al ₂ O ₃ /p-Si Interface State Spectrum. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H362		27
20	A deep-level transient spectroscopy study of silicon interface states using different silicon nitride surface passivation schemes. <i>Applied Physics Letters</i> , 2010 , 96, 103507	3.4	20
19	Zero-Temperature-Coefficient of planar and MuGFET SOI devices 2010 ,		3
18	Effect of rotation, gate-dielectric and SEG on the noise behavior of advanced SOI MuGFETs. <i>Solid-State Electronics</i> , 2010 , 54, 178-184	1.7	9
17	Is there an impact of threading dislocations on the characteristics of devices fabricated in strained-Ge substrates?. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, 1912-1917		16
16	Study of metal-related deep-level defects in germanide Schottky barriers on n-type germanium. <i>Journal of Applied Physics</i> , 2008 , 104, 023705	2.5	22

15	Novel, Effective and Cost-Efficient Method of Introducing Fluorine into Metal/Hf-based Gate Stack in MuGFET and Planar SOI Devices with Significant BTI Improvement 2007 ,		12
14	Impact of the gate-electrode/dielectric interface on the low-frequency noise of thin gate oxide n-channel metal-oxide-semiconductor field-effect transistors. <i>Solid-State Electronics</i> , 2007 , 51, 627-632	1.7	13
13	Low-Frequency Noise Assessment of Silicon Passivated Ge pMOSFETs With TiN/TaN/ HfO_2 Gate Stack. <i>IEEE Electron Device Letters</i> , 2007 , 28, 288-291	4.4	27
12	Reliability Comparison of Triple-Gate Versus Planar SOI FETs. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 2351-2357	2.9	43
11	The temperature mobility degradation influence on the zero temperature coefficient of partially and fully depleted SOI MOSFETs. <i>Microelectronics Journal</i> , 2006 , 37, 952-957	1.8	12
10	Gate electrode effects on low-frequency (1/f) noise in p-MOSFETs with high- κ dielectrics. <i>Solid-State Electronics</i> , 2006 , 50, 992-998	1.7	26
9	Tunneling 1/f noise in 5 nm HfO_2 /2.1 nm SiO_2 gate stack n-MOSFETs. <i>Solid-State Electronics</i> , 2005 , 49, 702-707	1.7	28
8	Low-Frequency Noise Performance of HfO_2 -Based Gate Stacks. <i>Journal of the Electrochemical Society</i> , 2005 , 152, F115	3.9	33
7	Characterization of Oxide Precipitates in Heavily B-Doped Silicon by Infrared Spectroscopy. <i>Journal of the Electrochemical Society</i> , 2004 , 151, G598	3.9	8
6	The 1/f ^{1.7} noise in submicron SOI MOSFETs with 2.5 nm nitrided gate oxide. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 2367-2370	2.9	17
5	On the flicker noise in submicron silicon MOSFETs. <i>Solid-State Electronics</i> , 1999 , 43, 865-882	1.7	236
4	Impact of silicidation on the excess noise behaviour of mos transistors. <i>Solid-State Electronics</i> , 1995 , 38, 1893-1897	1.7	42
3	Deep-level transient spectroscopy of detector-grade high-resistivity float-zone silicon. <i>Journal of Electronic Materials</i> , 1992 , 21, 533-541	1.9	5
2	The determination of deep level concentrations in high resistivity semiconductors by DLTS, with special reference to germanium. <i>Journal Physics D: Applied Physics</i> , 1985 , 18, 2041-2058	3	19
1	Defect Characterization in High-Electron-Mobility Transistors with Regrown p-GaN Gate by Low-Frequency Noise and Deep-Level Transient Spectroscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2100227	1.6	2